

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	4	hoff near andrew.in.	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 11:05	
2	BRS	L2	1105	438/778.ccls.	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 11:06	
3	BRS	L3	12	2 and ((sic) near substrate)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 11:07	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	2764	((sic) near substrate)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 11:07	
5	BRS	L5	7906 6	((sic) near substrate) or (silicon near carbide) or (silicon-carbide))	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 11:08	
6	BRS	L6	7906 6	((sic) near substrate)) or ((silicon near carbide) or (silicon-carbide))	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 11:09	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L7	2765	((sic) near substrate)) or ((silicon near carbide) or (silicon-carbide)) near25 ((electric near filed))	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:09	
8	BRS	L8	2939	((sic) near substrate)) or ((silicon near carbide) or (silicon-carbide)) near25 ((electric near field))	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:09	
9	BRS	L9	2765	((sic) near substrate)) or ((silicon near carbide) or (silicon-carbide)) near25 ((frequency near3 electric near field))	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:10	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	2765	((sic) near substrate)) or ((silicon near carbide) or (silicon-carbide)) near25 ((frequency near electric near field))	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:10	
11	BRS	L11	2765	((sic) near substrate)) or ((silicon near carbide) or (silicon-carbide)) near25 ((frequency near electric near field)) near15 (gas)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:10	
12	BRS	L12	2764	((sic) near substrate)) or ((silicon near carbide) or (silicon-carbide)) near25 ((frequency near electric near field)) near15 (excited near gas)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:10	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	2764	((sic) near substrate)) or ((silicon near carbide) or (silicon-carbide)) near25 ((frequency near electric near field)) near15 (excited near gas) near15 (energy)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM-TDB	2004/11/29 11:11	
14	BRS	L14	2764	((sic) near substrate)) or ((silicon near carbide) or (silicon-carbide)) near25 ((frequency near electric near field)) near15 ((excited near gas) near15 (energy))	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM-TDB	2004/11/29 11:11	
15	BRS	L15	2764	((sic) near substrate)) or ((silicon near carbide) or (silicon-carbide)) near25 ((frequency near electric near field)) near15 ((excited near gas) near15 (energy)) near25 (silicon near oxide near film)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM-TDB	2004/11/29 11:12	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
16	BRS	L16	2764	((sic) near substrate)) or ((silicon near carbide) or (silicon-carbide)) near25 ((frequency near electric near field)) near15 ((excited near gas) near15 (energy)) near25 (silicon near oxide near film) near15 (afterglow)	US-PGPU B; USPAT; EPO; JPO; DERWENT; IBM-TDB	2004/11/29 11:12	
17	BRS	L17	2764	((sic) near substrate)) or ((silicon near carbide) or (silicon-carbide)) near25 (((frequency near electric near field)) near15 ((excited near gas) near15 (energy)) near25 (silicon near oxide near film) near15 (afterglow))	US-PGPU B; USPAT; EPO; JPO; DERWENT; IBM-TDB	2004/11/29 11:13	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
18	BRS	L18	0	((frequency near electric near field)) near15 ((excited near gas) near15 (energy)) near25 (silicon near oxide near film) near15 (afterglow))	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:13	
19	BRS	L19	0	((frequency near electric near field) near15 (gas) near15 (energy) near25 (silicon near oxide near film) near15 (afterglow))	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:13	
20	BRS	L20	0	((electric near field) near15 (gas) near15 (energy) near25 (silicon near oxide near film) near15 (afterglow))	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:14	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
21	BRS	L21	0	(electric near field) near15 (gas) near15 (energy) near25 (silicon near oxide near film)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:14	
22	BRS	L22	24	(electric near field) near15 (gas) near25 (silicon near oxide near film)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:14	
23	BRS	L23	0	(electric near field) near15 (gas) near25 (silicon near oxide near film) near15 (sic)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:15	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
24	BRS	L24	0	(electric near field) near15 (gas) near25 (silicon near oxide near film) near15 (carbide)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:15	
25	BRS	L25	38	(electric near field) near15 (gas) near15 (carbide)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:15	
26	BRS	L26	29	(electric near field) near15 (gas) near15 (silicon near carbide)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:19	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
27	BRS	L27	0	(electric near field) near15 (gas) near15 (silicon-carbide)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/29 11:19	
28	BRS	L28	7	(electric near field) near15 (gas) near15 (sic)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/29 11:20	
29	BRS	L29	0	(electric near field) near15 (excited near gas) near15 (sic)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/29 11:20	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
30	BRS	L30	0	(electric near field) near15 (oxidiz\$3 near gas) near15 (sic)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:21	
31	BRS	L32	0	(oxidiz\$3 near gas) near15 (sic) same (electric near field)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:21	
32	BRS	L31	23	(oxidiz\$3 near gas) near15 (sic)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_TDB	2004/11/29 11:24	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
33	BRS	L33	3672	(gas) near15 (sic)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 11:24	
34	BRS	L34	362	((gas)) near15 ((sic or silicon near carbide) near (wafer or substrate))	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 12:33	
35	BRS	L35	1123 1	(electric near field) near15 (energy)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 12:21	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
36	BRS	L36	214	(frequency near electric near field) near15 (energy)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 12:22	
37	BRS	L37	17	(frequency near electric near field) near15 (energy) near15 (substrate or wafer)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 12:24	
38	BRS	L38	826	(electric near field) near15 (energy) near15 (substrate or wafer)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 12:25	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
39	BRS	L39	79	(electric near field) near15 (energy) near15 (gas) near15 (substrate or wafer)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 12:25	
40	BRS	L40	17	((gas)) near15 ((sic or silicon near carbide) near (wafer or substrate)) near15 (tube)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 12:40	
41	BRS	L41	0	((gas)) near15 ((sic or silicon near carbide) near (wafer or substrate)) near15 (tube) near15 (furnace near15 pump)	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 12:40	

	U	1	PT	P	Document ID	Issue Date	Page s	Title
1					US 2003000806 9 A1	20030109	11	Dual frequency plasma enhanced chemical vapor deposition of silicon carbide layers
2					US 2002013530 8 A1	20020926	19	Plasma process and apparatus
3					US 6589888 B2	20030708	11	Dual frequency plasma enhanced chemical vapor deposition of silicon carbide layers
4					US 6465366 B1	20021015	12	Dual frequency plasma enhanced chemical vapor deposition of silicon carbide layers
5					JP 58185418 A	19831029	3	DEPOSITION OF THICK CARBON FILM

	U	1	PT	P	Document ID	Issue Date	Page s	Title
6	X				JP 03124059 A	19910527	22	Semiconductor memory with cell having cylindrical type capacitors - having fins on outer periphery of central electrode increasing surface area of signal storage electrode
7	X				JP 03124032 A	19910527	14	Formation of silicon carbide - includes depositing accelerated carbon(contg.) ions into silicon(III) crystal irradiated with ionic or atomic hydrogen and heat treating